

3FT4C/F/M/U

主要参数 MAIN CHARACTERISTICS

$I_{T(RMS)}$	4A
V_{DRM}	600V or 800V
I_{GT}	10mA

用途

- 交流开关
- 相位控制

产品特性

- 玻璃钝化芯片，高可靠性和一致性
- 低通态电流和高浪涌电流能力
- 环保 RoHS 产品

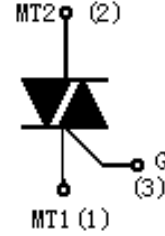
APPLICATIONS

- AC switching
- Phase control

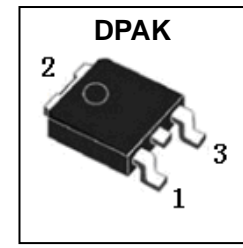
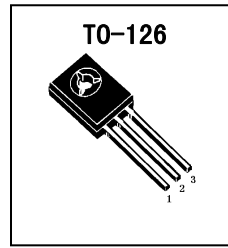
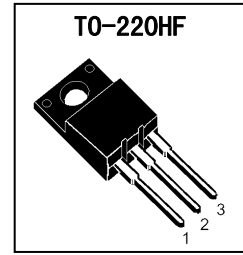
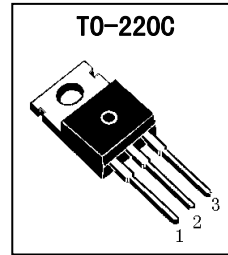
FEATURES

- Glass-passivated mesa chip for reliability and uniform
- Low on-state voltage and High I_{TSM}
- RoHS products

封装 Package



序号 Pin	引线名称 Description
1	主电极 1 MT1
2	主电极 2 MT2
3	门极 G



订货信息 ORDER MESSAGES

订货型号 Order code	印记 Marking	封装 Package	包装 Packaging
3FT4C-O-C-N-B	3FT4C	TO-220C	条管 Tube
3FT4F-O-HF-N-B	3FT4F	TO-220HF	条管 Tube
3FT4M-O-M-N-C	3FT4M	TO-126	袋装 Bag
3FT4U-O-U-B-A	3FT4U	DPAK	编带 Tape

概述 GENERAL DESCRIPTION

3FT4C/F/M/U是玻璃钝化芯片结构的四象限双向晶闸管。器件封装形式有TO-220C、TO-220HF、TO-126和DPAK。

3FT4C/F/M/U are Glass passivated four quadrant triacs. Available packages are TO-220C、TO-220HF、TO-126 and DPAK.



绝对最大额定值 ABSOLUTE RATINGS (T_c=25℃)

项 目 Parameter	符 号 Symbol	试 验 条 件 Condition	数 值 Value	单 位 Unit
重复峰值断态电压 Repetitive peak off-state voltage	V _{DRM}		±600 ±800	V
通态方均根电流 On-state RMS current	I _{T(RMS)}	full sine wave	4	A
非重复浪涌峰值通态电流 Non-repetitive surge peak on-state current	I _{TSM}	full sine wave ,t=20ms	25	A
		full sine wave ,t=16.7ms	27	A
		I ² t	t=10ms	3.1
通态电流临界上升率 Repetitive rate of rise of on-state current after triggering	di/dt	I _{TM} =6A, I _G =0.2A, di _G /dt=0.2A/μ s	50	A/μ s
峰值门极电流 Peak gate current	I _{GM}		2	A
峰值门极电压 Peak gate voltage	V _{GM}		5	V
峰值门极功率 Peak gate power	P _{GM}		5	W
平均门极功率 Average gate power	P _{G(AV)}	over any 20ms period	0.5	W
存储温度 Storage temperature	T _{stg}		-40~150	℃
操作结温 Operation junction temperature	T _{VJ}		125	℃

电特性 ELECTRICAL CHARACTERISTIC (T_C=25°C)

项 目 Parameter	符 号 Symbol	测 试 条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit	
峰值重复断态电流 Peak Repetitive Blocking Current	I _{DRM}	V _{DM} =V _{DRM} , T _j =25°C, gate open	-	-	10	μ A	
		V _{DM} =V _{DRM} , T _j =125°C, gate open	-	-	0.5	mA	
峰值通态电压 Peak on-state voltage	V _{TM}	I _{TM} =5A	-	-	1.7	V	
门极触发电流 Gate trigger current	I _{GT}	V _{DM} =12V, R _L =100 Ω	MT1(-),MT2(+),G(+)	-	-	10	mA
			MT1(-),MT2(+),G(-)	-	-	10	mA
			MT1(+),MT2(-),G(-)	-	-	10	mA
			MT1(+),MT2(-),G(+)	-	-	45	mA
门极触发电压 Gate trigger voltage	V _{GT}	V _{DM} =12V, R _L =100 Ω	MT1(-),MT2(+),G(+)	-	-	1.5	V
			MT1(-),MT2(+),G(-)	-	-	1.5	V
			MT1(+),MT2(-),G(-)	-	-	1.5	V
			MT1(+),MT2(-),G(+)	-	-	2.0	V
维持电流 Holding current	I _H	V _{DM} =12V, I _{GT} =0.1A	-	-	15	mA	
擎住电流 Latching current	I _L	V _{DM} =12V, I _{GT} =0.1A	-	-	30	mA	
断态临界电压上升率 Rise of off- state voltage	dV/dt	V _{DM} =67% V _{DRM(MAX)} , T _j =125°C, gate open	-	50	-	V/μ s	
门极开通时间 Gate controlled turn-on time	t _{gt}	I _{TM} =6A, V _{DM} =V _{DRM(MAX)} , I _G =0.1A, dI _G /dt=5A/μ S	-	2	-	μ s	

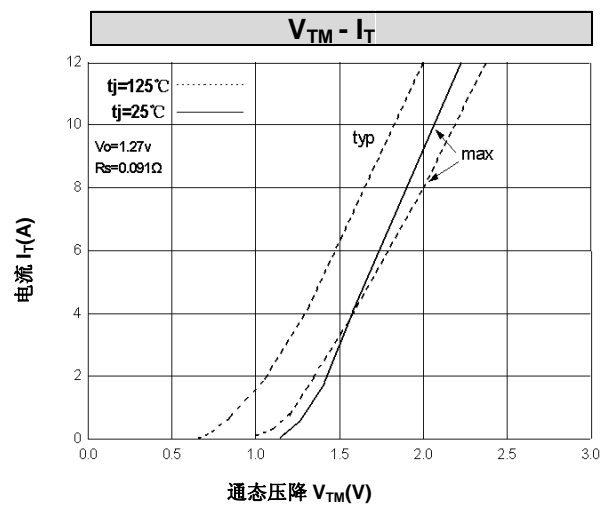
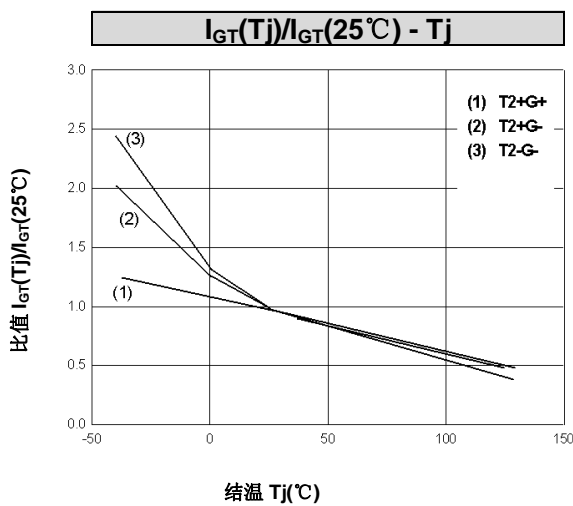
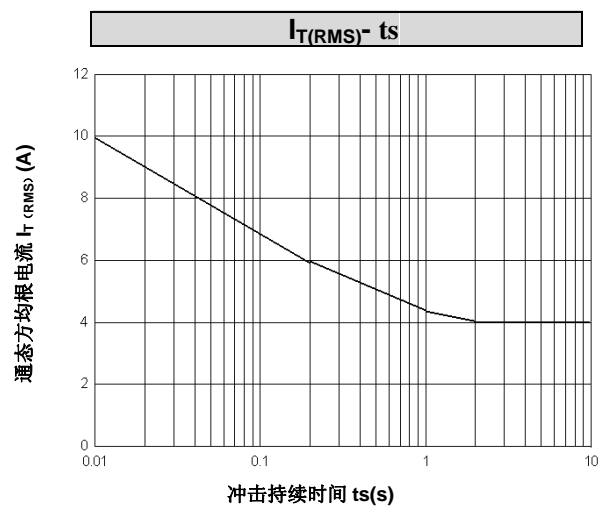
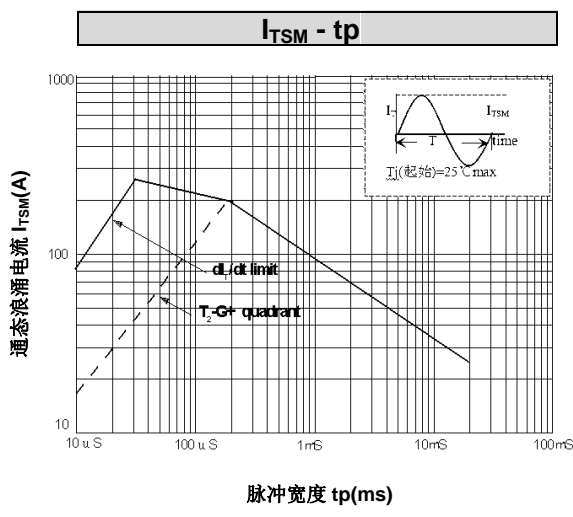
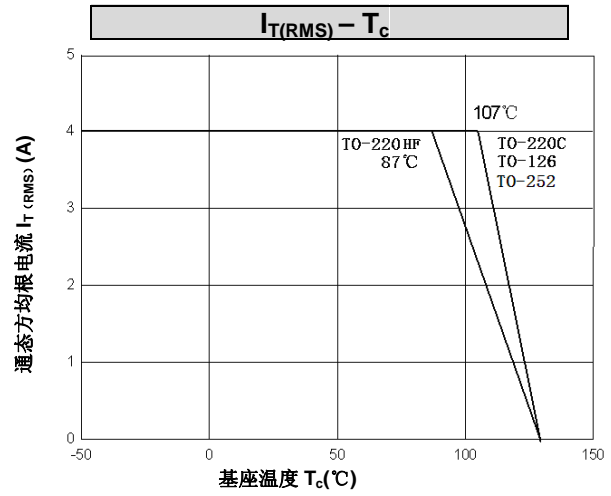
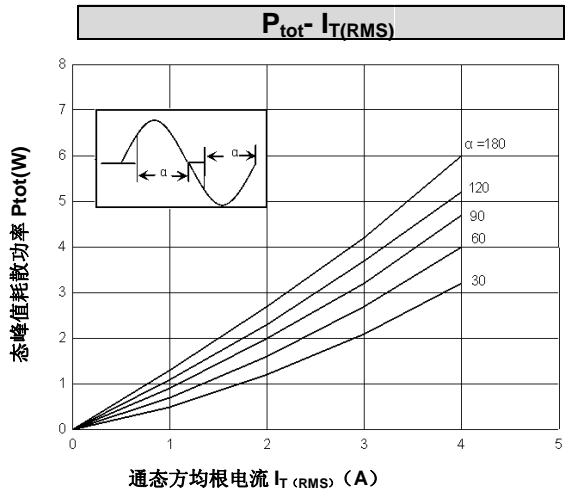
热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	条 件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
结到管壳的热阻 Thermal resistance junction to case	R _{th(j-c)}	full cycle (TO-220C/TO-126/TO-252)			3.0	°C/W
		full cycle(TO-220HF)			5.5	°C/W

电绝缘特性 ELECTRICAL ISOLATION

项 目 Parameter	符 号 Symbol	条 件 Condition	数 值 Value	单 位 Unit
绝缘电压 Isolation voltage	V _{ISOL}	1 minute, leads to mounting tab TO-220HF	2000	V

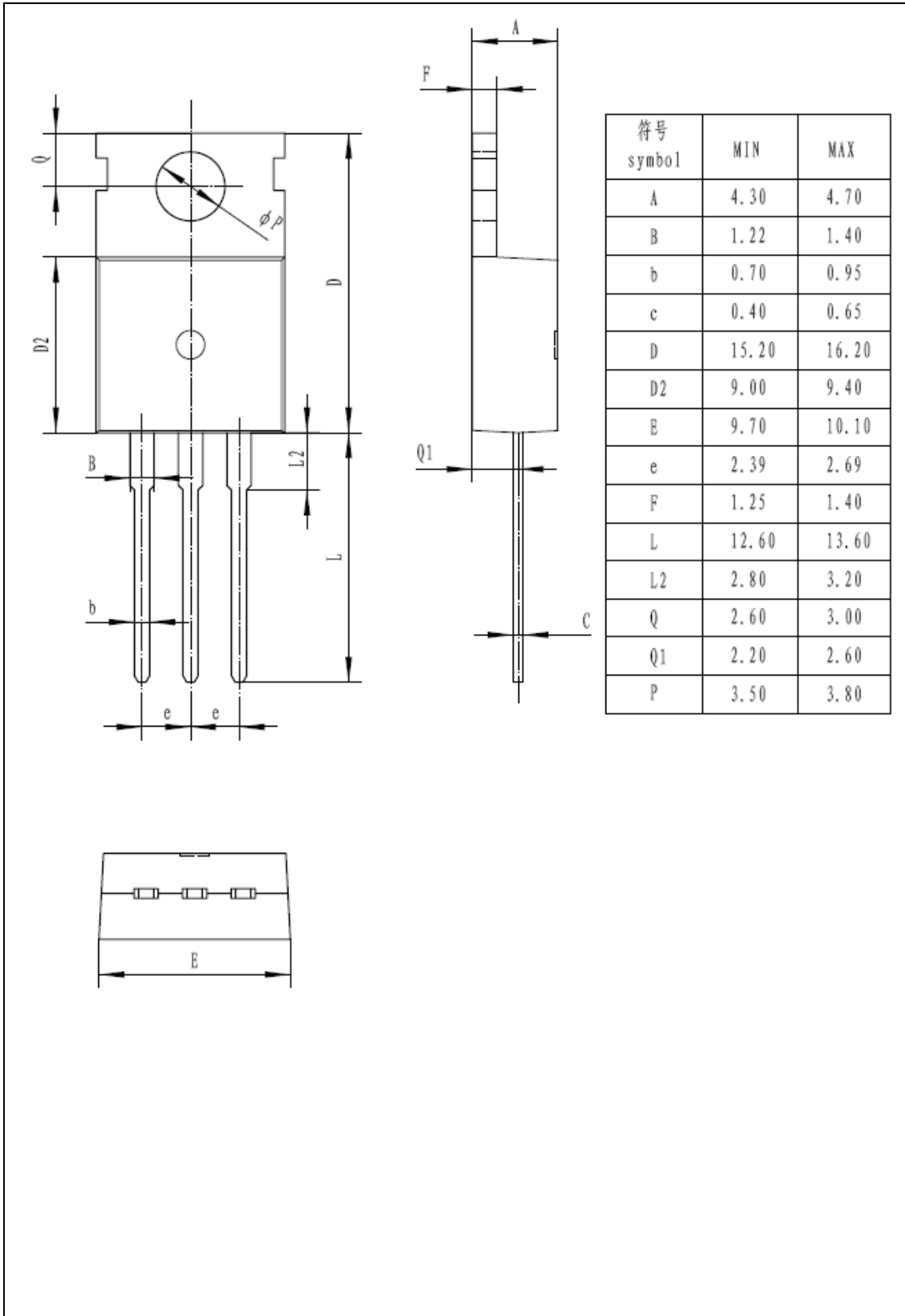
特征曲线 ELECTRICAL CHARACTERISTICS (curves)



外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

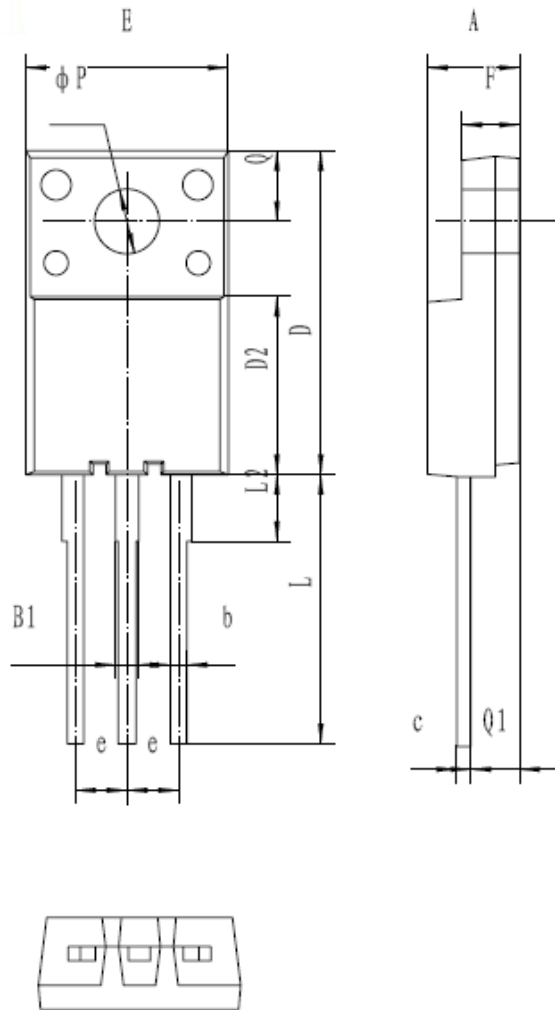
单位 Unit : mm



外形尺寸 PACKAGE MECHANICAL DATA

TO-220HF

单位 Unit : mm



符号 symbol	MIN	MAX
A	4.0	5.0
B1	0.87	1.27
b	0.72	0.92
c	0.5	0.7
D	15.0	16.5
D2	7.8	9.4
E	9.62	10.62
e	2.54 TYP	
F	2.3	3.3
L	13.0	14.0
L2	3.1	3.5
ϕP	3.0	3.4
Q	3.15	3.55
Q1	2.2	2.5

外形尺寸 PACKAGE MECHANICAL DATA

DPAK

单位 Unit : mm

